



# GPDG3115

## RECTIFIER DIODE

Low profile ceramic package

<b>VOLTAGE UP TO</b>	<b>2200 V</b>
<b>AVERAGE CURRENT</b>	<b>1150 A</b>
<b>SURGE CURRENT</b>	<b>14 kA</b>

### BLOCKING CHARACTERISTICS

Characteristic	Conditions	Value
V <sub>RRM</sub>	Repetitive peak reverse voltage	2200 V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage	2300 V
I <sub>RRM</sub>	Repetitive peak reverse current, max.	V <sub>RRM</sub> , single phase, half wave, T <sub>j</sub> = T <sub>jmax</sub>
		30 mA

### FORWARD CHARACTERISTICS

I <sub>F(AV)</sub>	Average forward current	Sine wave, 180° conduction, T <sub>h</sub> = 55°C	1150 A
I <sub>F(RMS)</sub>	R.M.S. forward current	Sine wave, 180° conduction, T <sub>h</sub> = 55°C	1806 A
I <sub>FSM</sub>	Surge forward current	Non rep. half sine wave, 50 Hz, V <sub>R</sub> = 0 V, T <sub>j</sub> = T <sub>jmax</sub>	14 kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination		980 kA <sup>2</sup> s
V <sub>F(TO)</sub>	Threshold voltage	T <sub>j</sub> = T <sub>jmax</sub>	0.925 V
r <sub>F</sub>	Forward slope resistance	T <sub>j</sub> = T <sub>jmax</sub>	0.258 mΩ
V <sub>FM</sub>	Peak forward voltage, max	Forward current I <sub>F</sub> = 1200 A, T <sub>j</sub> = T <sub>jmax</sub>	1.235 V

### SWITCHING CHARACTERISTICS

Q <sub>rr</sub>	Reverse recovery charge, typ	T <sub>j</sub> = T <sub>jmax</sub> , I <sub>F</sub> = 2000 A, di/dt = -5 A/μs	μC
I <sub>rr</sub>	Reverse recovery current	V <sub>R</sub> = 100 V	A
t <sub>rr</sub>	Reverse recovery time		μs
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = T <sub>jmax</sub> , di/dt = A/μs	V

### THERMAL AND MECHANICAL CHARACTERISTICS

R <sub>th(j-c)</sub>	Thermal resistance (junction to case)	Double side cooled	0.038 °C/W
R <sub>th(c-h)</sub>	Thermal resistance (case to heatsink)	Double side cooled	0.012 °C/W
T <sub>jmax</sub>	Max operating junction temperature		150 °C
T <sub>stg</sub>	Storage temperature		-40 / 150 °C
F	Clamping force ± 10%		9 kN
	Mass		110 g